



SANYO Semiconductors

## DATA SHEET

N-Channel Silicon MOSFET

# ECH8618 — General-Purpose Switching Device Applications

## Features

- Ultrahigh-speed switching.
- 4V drive.
- Composite type, facilitating high-density mounting.

## Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		100	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		2	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	12	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm²×0.8mm) 1unit	1.3	W
Total Dissipation	P <sub>T</sub>	Mounted on a ceramic board (900mm²×0.8mm)	1.5	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	100			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1A	1.6	2.7		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =10V		200	260	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =0.5A, V <sub>GS</sub> =4V		230	325	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, f=1MHz		650		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =20V, f=1MHz		42		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =20V, f=1MHz		29		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		11.5		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		4.9		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		67		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		23		ns

Marking : FL

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# ECH8618

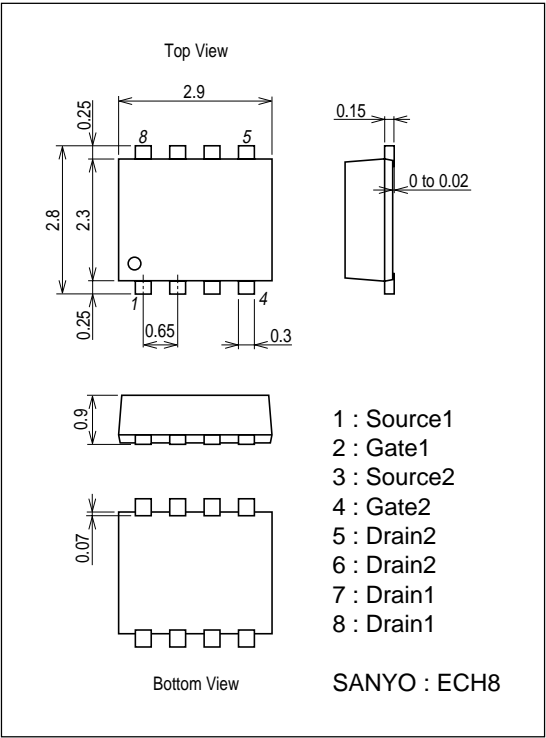
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =2A		13.8		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =2A		2.1		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =2A		3		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =2A, V <sub>GS</sub> =0V		0.80	1.2	V

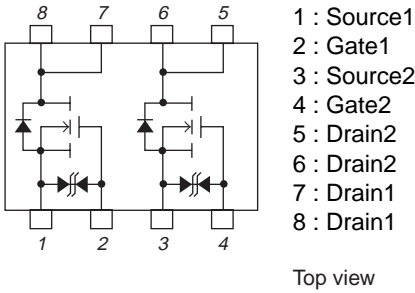
## Package Dimensions

unit : mm

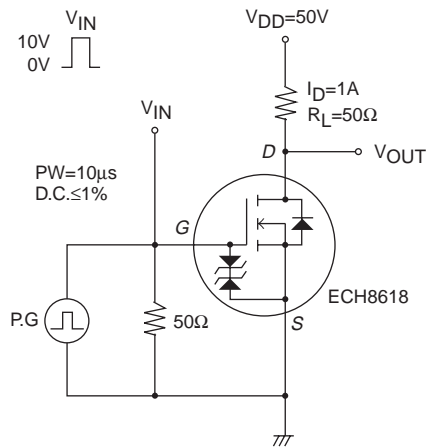
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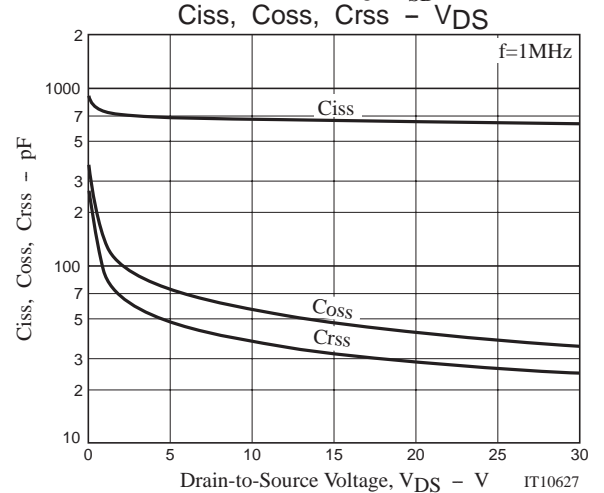
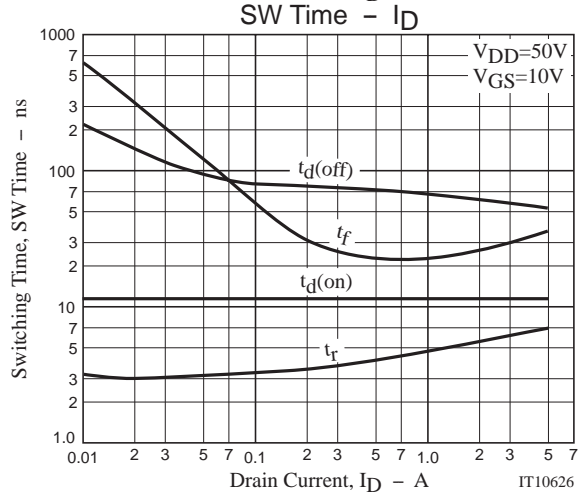
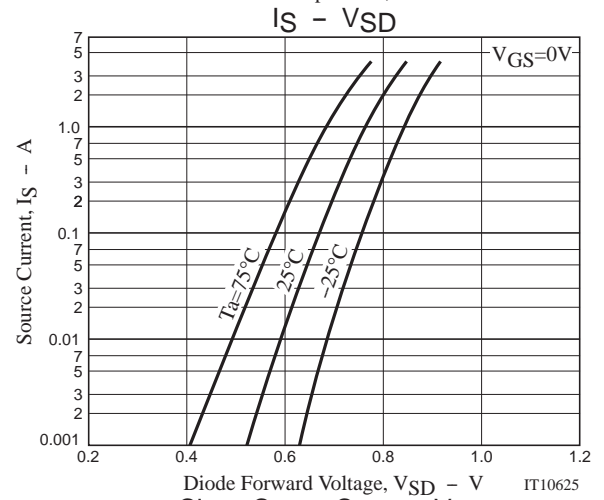
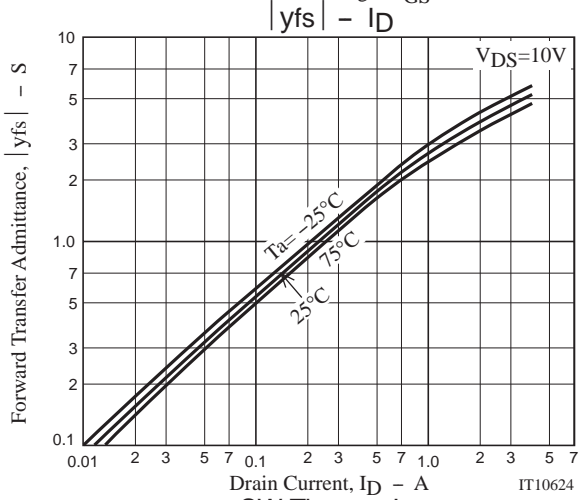
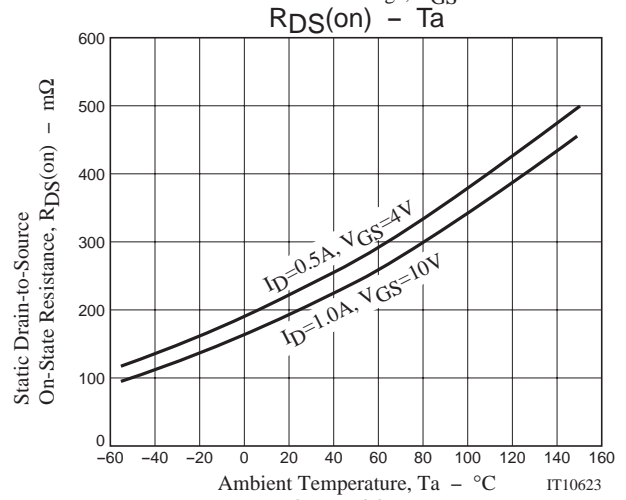
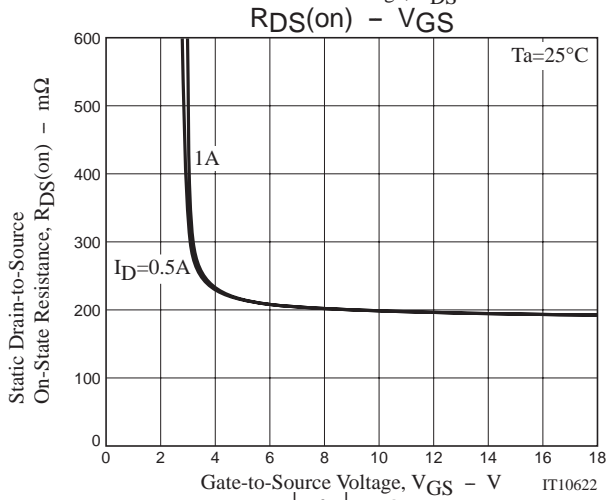
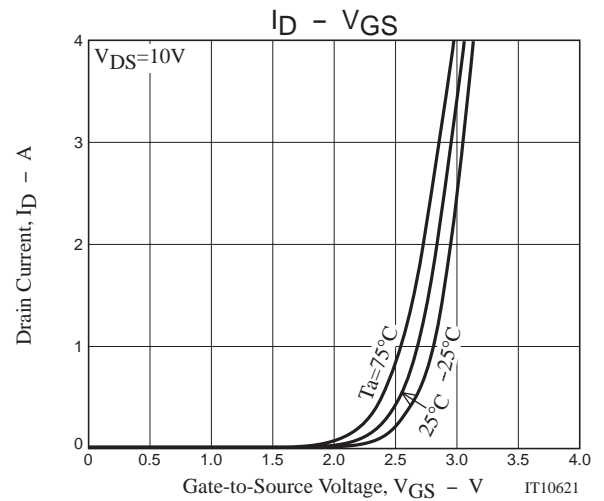
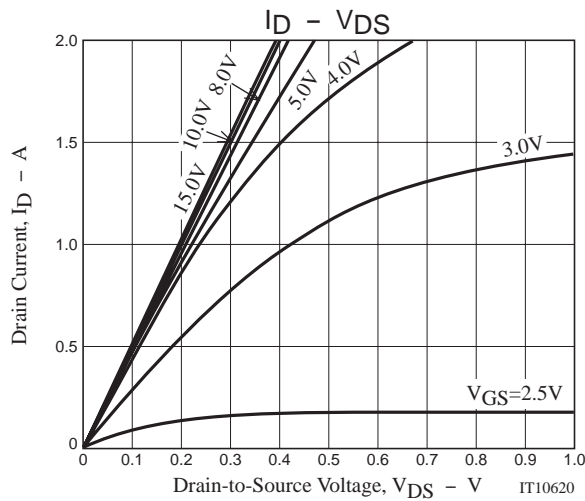


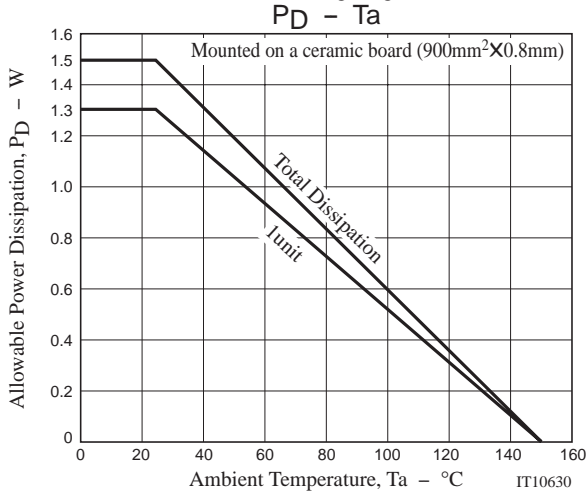
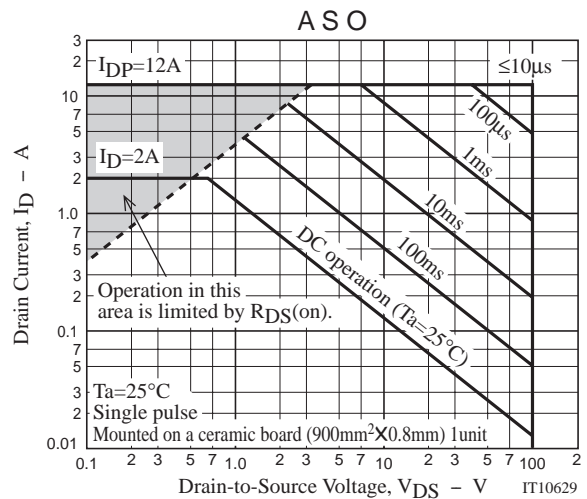
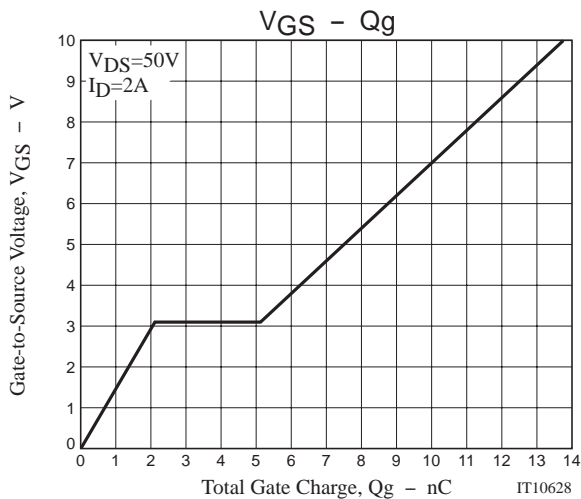
## Electrical Connection



## Switching Time Test Circuit







Note on usage : Since the ECH8618 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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